

App. Serial No. 10/530,063
Docket No.: BE 020027 US

In the Claims:

Please amend claim 1 as indicated below. This listing of claims replaces all prior versions.

1. *(Currently Amended)* A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition using source gases, and including employing nitrogen or a noble gas as a carrier gas.
2. *(Previously presented)* A method as claimed in claim 1, the method forming an epitaxial layer based on at least one of the following: silicon, germanium, and carbon.
3. *(Original)* A method as claimed in claim 2, wherein the epitaxial layer comprises $\text{Si}_{1-y}\text{C}_y$.
4. *(Original)* A method as claimed in claim 2, wherein the epitaxial layer comprises a SiGe epitaxial layer.
5. *(Original)* A method as claimed in claim 2, wherein the epitaxial layer comprises $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$.
6. *(Original)* A method as claimed in claim 2, wherein the epitaxial layer comprises a silicon epitaxial layer.
7. *(Previously presented)* A method as claimed in claim 2, which is carried out at a temperature that facilitates a CVD growth rate of an epitaxial layer that is substantially greater than a CVD growth rate of such an epitaxial layer using hydrogen as a carrier gas.
8. *(Previously presented)* A method as claimed in claim 2, which is carried out at a temperature of less than about 600°C.

Claims 9-16 (*Cancelled*).

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17. (*Previously presented*) A method as claimed in claim 3, which is carried out at a temperature of less than about 600°C.

18. (*Previously presented*) A method as claimed in claim 4, which is carried out at a temperature of less than about 600°C.

19. (*Previously presented*) A method as claimed in claim 5, which is carried out at a temperature of less than about 600°C.

20. (*Previously presented*) A method as claimed in claim 6, which is carried out at a temperature of less than about 600°C.